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ANTONIO ABRAMO

CURRICULUM VITAE E PUBBLICAZIONI

Il sottoscritto Antonio Abramo autorizza il trattamento di tutti dati personali qui di seguito riportati ai sensi del Decreto Legislativo 30 giugno 2003, n. 196 “Codice in materia di protezione dei dati personali”.

INDICE

CONTATTI

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CRONOLOGIA ESSENZIALE

2020 -	Membro del Comitato Tecnico Spin-off dell'Università di Udine
2017 - 2019	Delegato del Rettore al Tavolo Tecnico per la creazione del Competence Center Triveneto di I4.0
2017 - 2018	Delegato del Rettore per il Trasferimento della Conoscenza
2017 - 2019	Membro designato del Comitato di Gestione della Fondazione Rino Snaidero
2017 -	Membro del Comitato Tecnico di Valutazione Regione Friuli-Venezia Giulia
2016 - 2017	Delegato del Rettore per i Brevetti
2013 - 2016	Membro della Commissione Tecnica Brevetti dell'Università degli Studi di Udine
2008 - 2018	Direttore di Ricerca - ETH Lab, Eurotech Group (http://www.eurotech.com)
2008 - 2013	Direttore Scientifico - PTLab, Agemont, (http://www.pervasivelab.agemont.it)
2000 -	Professore Associato di Elettronica, Università degli Studi di Udine
1997 - 2000	Ricercatore di Elettronica, Università degli Studi di Udine
1995 - 1997	PostDoc - Dipartimento di Fisica - Università degli Studi di Modena
1995	Ph.D. in Ingegneria Elettronica - Università degli Studi di Bologna
1990	Inizio attività scientifica - DEIS, Università degli Studi di Bologna
1987	Laurea in Ingegneria Elettronica (magna cum laude) - Università degli Studi di Bologna
1962	Nato a Bologna il 16 agosto 1962

ESPERIENZE INTERNAZIONALI

2000	Visiting Professor, Center for Integrated Systems, Stanford University, Palo Alto (CA), USA
1993 - 1994	Visiting Scholar, Technology Research Department, AT&T Bell Labs, Murray Hill (NJ),USA
1992	Summer Job, Technology CAD Group, Intel Corporation, Santa Clara (CA), USA
1991	Visiting Scholar, Technology Research Department, AT&T Bell Labs, Murray Hill (NJ),USA

ATTIVITÀ DIDATTICA

Sistemi Immersi, Architetture a Microprocessore, Architetture Parallele, Elettronica, Reti Neurali.

NOTE

Antonio Abramo è Senior Member dell'IEEE.

ICST 2011 - International Conference on Sensing Technology, Palmerston North, NZ, Nov. 2011:
Membro del Comitato Scientifico Internazionale.

IEDM 2003 - International Electron Device Meeting, Washington, D.C., USA, Dic. 2003:
Chairman del Comitato Tecnico "Modeling and Simulation".

IEDM 2002 - International Electron Device Meeting, S. Francisco (CA), USA - Dic. 2002:
Membro del Comitato Tecnico "Modeling and Simulation".

IEDM 2001 - International Electron Device Meeting, Washington, D.C., USA, Dic. 2001:
Membro del Comitato Tecnico "Modeling and Simulation".

FUND RISING

- Cluster Italiano su "Assisted Living" - Azione di Ricerca su "Smart Cities / Smart Environments"
  Progetto D4All; Finanziamento di Progetto: 11 MEuro; Finanziamento di Unità: 580 kEuro; Durata: tre anni)
- Piattaforma Tecnologica Europea ARTEMIS
  Progetto nSHIELD; Finanziamento di Progetto: 13 MEuro; Finanziamento di Unità: 360 kEuros; Durata: tre anni)
- Piattaforma Tecnologica Europea ENIAC
  Progetto E2SG; Finanziamento di Progetto: 36 MEuro; Finanziamento di Unità: 1.2 MEuro; Finanziamento di Gruppo: 40 kEuro; Durata: tre anni)
- Piattaforma Tecnologica Europea ENIAC
  Progetto END; Finanziamento di Progetto: 12 MEuro; Finanziamento di Unità: 50 kEuro; Durata: tre anni)
- Progetto POR-FESR "Easyhome"
  Finanziamento di Progetto: 1,5 MEuro; Finanziamento di Unità: 190 kEuro; Durata: tre anni)
- Fondi Regionali su Legge Innovazione per la creazione di un Laboratorio di Tecnologie Pervasive
  (Finanziamento totale: 650 kEuro; Durata: tre anni)
- Progetto Nazionale PRIN su Autonomic Computing
  Finanziamento di Progetto: 132 kEuro; Finanziamento di Unità: 51 kEuro; Durata: due anni)

LISTA DELLE PUBBLICAZIONI

RIVISTE INTERNAZIONALI

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[IJ02] A. Abramo, F. Venturi, E. Sangiorgi, J.M. Higman, B. Riccò, "A numerical method to compute isotropic band models from anisotropic semiconductor band structures", IEEE Transaction on Computer-Aided Design, 12, 1327 (1993).

[IJ03] A. Abramo, L. Baudry, R. Brunetti, R. Castagné, M. Charef, F. Dessenne, P. Dolfus, R. Dutton, W.L. Engl, R. Fauquembergue, C. Fiegna, M.V. Fischetti, S. Galdin, N. Goldsman, M. Hackel, C. Hamaguchi, K. Hess, K. Hennacy, P. Hesto, J.M. Higman, T. Iizuka, C. Jungemann, Y. Kamakura, H. Kosina, T. Kunikiyo, S. Laux, H. Lin, C. Maziar, H. Mizuno, H.J. Peifer, S. Ramaswamy, N. Sano, P.G. Scrobohaci, S. Selberherr, M. Takenaka, T-W. Tang, K. Taniguchi, J.L. Thobel, R. Thoma, K. Tomizawa, M. Tomizawa, T. Vogelsang, S-L. Wang, X. Wang, C-S. Yao, P.D. Yoder, A. Yoshii, "A comparison of numerical solutions of the Boltzmann Transport Equation for high energy electron transport silicon", IEEE Transaction on Electron Devices, 41, 1646 (1994).

[IJ04] A. Abramo, R. Brunetti, C. Jacoboni, F. Venturi, E. Sangiorgi, "A multi-Band Monte Carlo approach to Coulomb interaction for device analysis", Journal of Applied Physics, 76, 5786 (1994).

[IJ05] A. Abramo, J. Bude, F. Venturi, M.R. Pinto, "Mobility simulation of a novel Si/SiGe FET structure", IEEE Electron Device Letters, 17, 59 (1996).

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[IJ07] A. Abramo, C. Fiegna, "Electron energy distributions in silicon structures at low applied voltages and high electric fields", Journal of Applied Physics, 80, 889 (1996).

[IJ08] P. Bordone, A. Abramo, R. Brunetti, M. Pascoli, C. Jacoboni, "Wigner-function for open systems with electron-phonon interaction", Physica Status Solidi B, 204, 303 (1997).

[IJ09] I. Ferretti, A. Abramo, R. Brunetti, C. Jacoboni, "Full-band Monte Carlo analysis of hot-carrier light emission in GaAs", Physica Status Solidi B, 204, 538 (1997).

[IJ10] C. Fiegna, A. Abramo, "Analysis of quantum effects in non-uniformly doped MOS structure", IEEE Transaction Electron Devices, 45, 877 (1998).

[IJ11] C. Jacoboni, A. Abramo, P. Bordone, R. Brunetti, M. Pascoli, "Application of the Wigner-function formulation to mesoscopic systems in presence of the electron-phonon interaction", VLSI Design, 8, 185 (1998).

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[IJ14] A. Abramo, A. Cardin, L. Selmi, E. Sangiorgi, "Two-dimensional quantum mechanical simulation of charge distribution in silicon MOSFETs", IEEE Transaction Electron Devices, 47, 1858 (2000).

[IJ15] J.-S. Goo, C.-H. Choi, A. Abramo, J.-G. Ahn, Z. Yu, T. H. Lee, R. W. Dutton, "Physical origin of the excess thermal noise in short channel MOSFETs", IEEE Electron Device Letters, 22, 101 (2001).

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"Analytical and numerical study of the impact of HALOS on short channel and hot carrier effects in scaled MOSFETs",
Solid State Electronics, 46, 429 (2002).

[IJ19] P. Palestri, A. Dalla Serra, L. Selmi, M. Pavesi , P. Rigolli, A. Abramo, F. Widdershoven, E. Sangiorgi,
"A comparative analysis of substrate current generation mechanisms in tunneling MOS capacitors",
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[IJ21] A. Abramo,
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[IJ22] D. Esseni, A. Abramo,
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"A mixed convex/non-convex distributed localization approach for the deployment of indoor positioning services",
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"The Correspondence Between deterministic and stochastic digital neurons: analysis and methodology",
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[IC03] A. Abramo, C. Fiegna, F. Venturi, R. Brunetti, E. Sangiorgi, C. Bergonzoni, B. Riccò,
"A new microscopic model for hole transport in silicon with application to sub-micron LDD MOSFETs",
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VI SB Micro Technical Digest, 18, Belo Horizonte (Brazil), Aug. 1991. (Invited paper)

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"An isotropic best-fitting band model for electrons and hole transport in Silicon",
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"Modeling of high energy electrons in n-MOSFETs",
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[IC07] F. Venturi, E. Sangiorgi, C. Fiegna, A. Abramo, F. Capasso,
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"Device simulation of small silicon MOSFET's using the Monte Carlo method",
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SISDEP Technical Digest, 181, Wien, (Austria), Sep. 1993.

[IC14] A. Ghetti, L. Selmi, E. Sangiorgi, A. Abramo, F. Venturi,
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[IC16] A. Abramo, J. Bude, F. Venturi, M.R. Pinto, E. Sangiorgi,
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SISPAD Technical Digest, 106, Erlangen, (Germany), Sep. 1995.

[IC17] A. Abramo, C. Fiegna, F. Venturi,
"Hot carrier effects in short MOSFETs at low applied voltages",
IEDM Technical Digest, 301, Washington, DC (USA), Dec. 1995.

[IC18] A. Abramo, P. Casarini, C. Jacoboni,
"Transmission properties of resonant cavities and rough quantum wells",
HCIS Technical Digest, 509, Chicago, IL (USA), Aug. 1996.

[IC19] C. Fiegna, A. Abramo,
"Optimization of channel profiles for ultra-short MOSFETs by quantum simulation",
IEDM Technical Digest, 815, S. Francisco, CA (USA), Dec. 1996.

[IC20] A. Abramo,
"A general purpose 2D Schrödinger solver with open/closed boundary conditions for quantum device analysis", SISPAD Technical Digest, 105, Boston, MA (USA), Sep. 1997.

[IC21] C. Fiegna, A. Abramo,
"Solution of 1-D Schrödinger and Poisson equations in single and double gate SOI MOS",
SISPAD Technical Digest, 93, Boston, MA (USA), Sep. 1997.

[IC22] A. Abramo, C. Fiegna, P. Casarini,
"Quantum effects in the simulation of conventional devices",
SISPAD Technical Digest, 121, Leuven, (Belgium), Sep. 1998. (Invited paper)

[IC23] C. Fiegna, A. Abramo, E. Sangiorgi,
"Simulation study of the impact of channel doping profiles on MOSFET analog performance",
ESSDERC Technical Digest, 688, Leuven, (Belgium), Sep. 1999.

[IC24] A. Abramo, A. Cardin, L. Selmi, E. Sangiorgi,
"Two-dimensional quantum simulation of silicon MOSFETs",
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[IC25] A. Todon, L. Selmi, A. Abramo, E. Sangiorgi,
"On the optimization of HALOs for 0.1 mm MOSFETs and below",
ISDRS Technical Digest, 41, Charlottesville, VA (USA), Dec. 1999.

[IC26] A. Abramo, A. Cardin, L. Selmi, E. Sangiorgi,
"Two-dimensional quantum mechanical aspects in the charge distribution of ULSI silicon MOSFETs", ULIS 2000 Technical Digest, 107, Grenoble, (FR), Jan 2000.

[IC27] A. Todon, L. Selmi, A. Abramo, E. Sangiorgi,
"Short channel and hot carrier performance of ULSI MOSFETs with halo structures",
ULIS 2000 Technical Digest, 111, Grenoble, (FR), Jan. 2000.

[IC28] A. Abramo, L. Selmi, Z. Yu, R. W. Dutton,
"Well-Tempered MOSFETs: 1D versus 2D quantum analysis",
SISPAD Technical Digest, 188, Seattle, WA (USA), Sep. 2000.

[IC29] A. Dalla Serra, A. Abramo, P. Palestri, L. Selmi,
"A comparison between semi-classical and quantum-mechanical escape-times for gate current calculations", ESSDERC Technical Digest, 340, Cork, (IR), Sep. 2000.

[IC30] P. Palestri, M. Pavesi, P. Rigolli,
L. Selmi, A. Dalla Serra, A. Abramo, F. Widdershoven, E. Sangiorgi,
"Impact ionization and photon emission in MOS capacitors and FETs",
IEDM Technical Digest, 97, S. Francisco, CA (USA), Dec. 2000.

[IC31] C. Fiegna, A. Abramo,
"Simulation of tunneling gate currents in ultra-thin SOI MOSFETs",
ISDRS Technical Digest, 110, Washington DC (USA), Dec. 2001.

[IC32] D. Esseni, A. Abramo,
"An improved model for electron mobility degradation by remote Coulomb scattering in ultra-thin oxide MOSFETs", ESSDERC Technical Digest, 183, Florence, (IT), Sep. 2002.

[IC33] R. Clerc, P. Palestri, A. Abramo,
"Investigation on convergence and stability of self-consistent Monte Carlo device simulations",
ESSDERC Technical Digest, 191, Florence, (IT), Sep. 2002.

[IC34] D. Esseni, A. Abramo, L. Selmi, E. Sangiorgi,
"Study of low field electron transport in ultra-thin single and double gate SOI MOSFETs",
IEDM Technical Digest, 719, S. Francisco, CA (USA), Dec. 2002.

[IC35] P. Palestri, D. Esseni, A. Abramo, R. Clerc, L. Selmi,
"Carrier quantization in SOI MOSFETs using an effective potential based Monte Carlo tool",
ESSDERC Technical Digest, 407, Lisbona, Sept. 2003.

[IC36] L. Lucci, D. Esseni, J. Loo, Y. Ponomarev, L. Selmi, A. Abramo, E. Sangiorgi,
"Quantitative assessment of mobility degradation by remote Coulomb scattering in ultra-thin oxide MOSFETs: measurements and simulations",
IEDM Technical Digest, 463, Washington, DC (USA), Dec. 2003.

[IC37] M. Martincigh, A. Abramo,
"A new stochastic neuron architecture for efficient FPGA implementation",
Austrochip Technical Digest, 95, Villach (Austria), Oct. 2004.

[IC38] A. Abramo, F. Blanchini, L. Geretti, C. Savorgnan,
"Mixed convex/non-convex distributed localization algorithm for the deployment of indoor positioning services", American Control Conference Technical Digest, 3967 (2007).

[IC39] C. Cavallotti, P. Merlino, E. Susilo, M. Vatteroni, P. Valdastri, A. Abramo, A. Menciassi, P. Dario,
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Eurosensors XXIV Technical Digest - Elsevier Procedia Engineering, 70 (2010).

[IC40] M. Vatteroni , C. Cavallotti, P. Valdastri, A. Menciassi, P. Dario, P. Merlino, A. Abramo,
"Vision system for high frame rate wireless capsule endoscope",
IEEE Sensors 2011 Technical Digest, 809 (2011).

[IC41] A. Guerrieri , L. Geretti, G. Fortino, A. Abramo,
"A service-oriented gateway for remote monitoring of building sensor networks",
IEEE CAMAD Technical Digest, 139 (2012).

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[IB01] A. Abramo, R. Brunetti, C. Fiegna, C. Jacoboni, B. Riccò, E. Sangiorgi, F. Venturi,
In “Monte Carlo simulation of silicon devices”,
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“Monte Carlo simulation of hot electrons in semiconductor devices”,
In “Hot electrons in semiconductors: physics and devices”,
Oxford University Press, N. Balkan Ed., 429 (1998). (Invited contribution)

[IB03] C. Fiegna, A. Abramo, E. Sangiorgi,
“Single- and double-gate SOI MOS structures for future ULSI: a simulation study”,
In “Future trends in microelectronics”, Wiley,
S. Luryi, J. Xu, A. Zaslavsky Eds., 115, (1999).

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“Advanced physically based device modeling for gate current and hot carrier phenomena in scaled MOSFETs”.
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“Modeling electron transport in MOSFET devices: evolution and state of the art”,
In “Advanced Device Modeling and Simulation”, Word Scientific Publishing Company,
T. Grasser Ed., 1, (2003). (Invited contribution)

[IB06] L. Geretti, A. Abramo,
“The synthesis of stochastic artificial neural network application using a genetic algorithm approach”.
In “Advances in Imaging and Electron Physics”, Wiley,
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[IB07] P. Merlino, A. Abramo,
“Deformation detection in Structural Health Monitoring”.
In “Developments in Sensing Technology for Structural Health Monitoring - Lecture Notes in Electrical Engineering”,
Springer, S.C. Mukhopadhyay Ed., 96, 41, (2011). (Invited contribution)

[IB08] P. Azzoni, K. Rantos, L. Geretti, A. Abramo, S. Gosetti,
“Biometric security domain”,
In “Measurable and composable security, privacy and dependability: the SHIELD Methodology”,
CRC Press, A. Fiaschetti, J. Noll, P. Azzoni, R. Uribeetxeberria Eds., 29 (2018).

[IB09] P. Azzoni, L. Geretti, A. Abramo, K. Stefanidis, J. Gialelis, A. Papalambrou, D. Serpanos, K. Rantos, A. Toma, N. Tassadaq, K. Dabcevic, C. Regazzoni, L. Marcenaro, M. Traversone, M. Cesena, S. Mignanti,
“Security, privacy, and dependability technologies”,
In “Measurable and composable security, privacy and dependability: the SHIELD Methodology”,
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RAPPORTI DI RICERCA

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AT&T Technical Memorandum, 11125-941004-22TM (38543), Oct. 4, 1994.

RIVISTE O CONTRIBUTI IN LIBRI NAZIONALI

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“Il miracolo dell'ubiquità”,
Rassegna Tecnica del Friuli-Venezia Giulia, 3, 19 (2006). (Invited paper)

[IN02] A. Abramo, R. Siagri,
“La tecnologia dell’informazione e i servizi per l’accessibilità”
In: “Accessibilità e valorizzazione dei beni culturali”, 382.4, 87 (Franco Angeli) (2012)

WORKSHOP INTERNAZIONALI

[IW01] A. Abramo,
“Quantum effects and limits in device scaling”
Workshop “Challenges in Advanced Electronic Device Simulation”
Seattle, WA (USA), Sep. 2000. (Invited panelist)

BREVETTI

[IP01] M. Carrer, C. De Alti, D. Rughetti, A. Abramo, S. Adami,
“System and method for trusted provisioning and authentication for networked devices in Cloud-based IOT/M2M platforms”, Sep. 29, 2016.